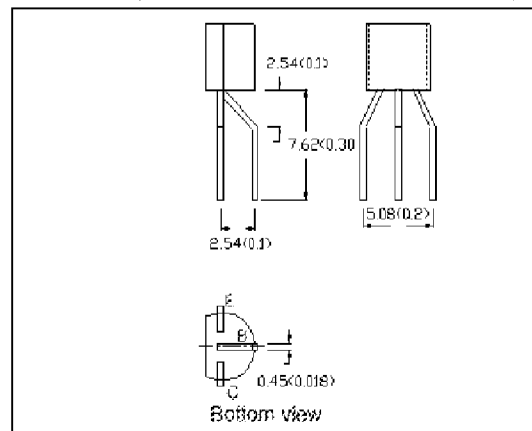


DESCRIPTION

CL117 is NPN silicon planar transistor designed for general purpose high voltage and video amplifier application.

TO-92F (LEAD FORM to MELF-002)



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	120V
Collector-Base Voltage	V _{CBO}	120V
Emitter-Base Voltage	V _{EBO}	5V
Collector Current Continuous	I _C	100mA
Total Power Dissipation @ Ta < 25°C	P _{tot}	625mW
Operating & Storage Junction Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta = 25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	LV _{CEO} *	120		V	I _C = 30mA	I _B = 0
Collector-Base Breakdown Voltage	BV _{CBO}	120		V	I _C = 0.1mA	I _E = 0
Emtter-Base Breakdown Voltage	BV _{EBO}	5		V	I _E = 0.01mA	I _C = 0
Collector Cutoff Current	I _{CBO}		100	nA	V _{CB} = 75V	I _E = 0
Emtter Cutoff Voltage	I _{EBO}		100	nA	V _{EB} = 4V	I _C = 0
D.C. Current Gain	H _{FE} *	25			I _C = 10mA	V _{CE} = 10V
		30			I _C = 30mA	V _{CE} = 10V
Collector-Emitter Saturation Voltage	V _{CE(sat)} *		0.2	V	I _C = 50mA	I _B = 5mA
Base-Emitter Saturation Voltage	V _{BE(sat)} *		0.9	V	I _C = 50mA	I _B = 5mA
Current Gain Bandwidth Product	f _T	40		MHz	I _C = 30mA	V _{CE} = 10V
Output Capacitance	C _{ob}	6	TYP.	pF	f = 20MHz	
					V _{CB} = 10V	f = 1MHz

* Pulse test : pulse width < 300μS, duty cycle < 1%.



MICRO ELECTRONICS LTD.

38, Hung To Road, Microtron Buiding, Kwun Tong, Kowloon, Hong Kong.

Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5

Jul-98